

# Kazuya Yamamura

## List of Publications by Year in descending order

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141  
papers

3,702  
citations

147566

31  
h-index

155451

55  
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143  
all docs

143  
docs citations

143  
times ranked

1584  
citing authors

#	ARTICLE	IF	CITATIONS
1	Cross-sectional observation of a weak boundary layer in polytetrafluoroethylene (PTFE) using scanning electron microscope. <i>Polymer Journal</i> , 2022, 54, 79-81.	1.3	10
2	Efficient and slurryless ultrasonic vibration assisted electrochemical mechanical polishing for 4H-SiC wafers. <i>Ceramics International</i> , 2022, 48, 7570-7583.	2.3	21
3	Adhesive-Free Adhesion between Plasma-Treated Glass-Cloth-Containing Polytetrafluoroethylene (GC-PTFE) and Stainless Steel: Comparison between GC-PTFE and Pure PTFE. <i>Polymers</i> , 2022, 14, 394.	2.0	8
4	Charge Utilization Efficiency and Side Reactions in the Electrochemical Mechanical Polishing of 4H-SiC (0001). <i>Journal of the Electrochemical Society</i> , 2022, 169, 023501.	1.3	3
5	Effects of polishing pressure and sliding speed on the material removal mechanism of single crystal diamond in plasma-assisted polishing. <i>Diamond and Related Materials</i> , 2022, 124, 108899.	1.8	19
6	Development of High-Efficiency Damage-Free Polishing Technology for Large-Sized Single Crystal Diamond Substrates by Plasma-Assisted Polishing. <i>Journal of the Japan Society for Precision Engineering</i> , 2022, 88, 133-136.	0.0	0
7	Separation of Neighboring Terraces on a Flattened Si(111) Surface by Selective Etching along Step Edges Using Total Wet Chemical Processing. <i>Langmuir</i> , 2022, 38, 3748-3754.	1.6	0
8	Nanocarbon-Induced Etching Property of Semiconductor Surfaces: Testing Nanocarbon's Catalytic Activity for Oxygen Reduction Reaction at a Single-Sheet Level. <i>ECS Journal of Solid State Science and Technology</i> , 2022, 11, 041001.	0.9	3
9	Slurryless Plasma-Assisted Polishing and Electrochemical Mechanical Polishing of Difficult to Polish Materials. <i>Journal of the Japan Society for Precision Engineering</i> , 2022, 88, 440-444.	0.0	0
10	Polishing and planarization of single crystal diamonds: state-of-the-art and perspectives. <i>International Journal of Extreme Manufacturing</i> , 2021, 3, 022003.	6.3	31
11	Atomic-scale insights into the origin of rectangular lattice in nanographene probed by scanning tunneling microscopy. <i>Physical Review B</i> , 2021, 103, .	1.1	5
12	Selective Etching of Semiconductor Surfaces by Catalytic Activity of Nanocarbon. <i>Vacuum and Surface Science</i> , 2021, 64, 352-357.	0.0	0
13	Atomic-scale and damage-free polishing of single crystal diamond enhanced by atmospheric pressure inductively coupled plasma. <i>Carbon</i> , 2021, 182, 175-184.	5.4	28
14	Dominant factors and their action mechanisms on material removal rate in electrochemical mechanical polishing of 4H-SiC (0001) surface. <i>Applied Surface Science</i> , 2021, 562, 150130.	3.1	17
15	Novel SiC wafer manufacturing process employing three-step slurryless electrochemical mechanical polishing. <i>Journal of Manufacturing Processes</i> , 2021, 70, 350-360.	2.8	18
16	Novel highly-efficient and dress-free polishing technique with plasma-assisted surface modification and dressing. <i>Precision Engineering</i> , 2021, 72, 224-236.	1.8	11
17	Comparison of surface and subsurface damage of mosaic single-crystal diamond substrate processed by mechanical and plasma-assisted polishing. <i>Diamond and Related Materials</i> , 2021, 119, 108555.	1.8	11
18	Effects of He and Ar Heat-Assisted Plasma Treatments on the Adhesion Properties of Polytetrafluoroethylene (PTFE). <i>Polymers</i> , 2021, 13, 4266.	2.0	10

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19	Comparison between adhesion properties of adhesive bonding and adhesive-free adhesion for heat-assisted plasma-treated polytetrafluoroethylene (PTFE). <i>Journal of Adhesion</i> , 2020, 96, 776-796.	1.8	21
20	Damage-free highly efficient plasma-assisted polishing of a 20-mm square large mosaic single crystal diamond substrate. <i>Scientific Reports</i> , 2020, 10, 19432.	1.6	21
21	Catalytic Properties of Chemically Modified Graphene Sheets to Enhance Etching of Ge Surface in Water. <i>Journal of Physical Chemistry C</i> , 2020, 124, 6121-6129.	1.5	12
22	High-quality plasma-assisted polishing of aluminum nitride ceramic. <i>CIRP Annals - Manufacturing Technology</i> , 2020, 69, 301-304.	1.7	12
23	Strong Biomimetic Immobilization of Pt-Particle Catalyst on ABS Substrate Using Polydopamine and Its Application for Contact-Lens Cleaning with H <sub>2</sub> O <sub>2</sub> . <i>Nanomaterials</i> , 2020, 10, 114.	1.9	5
24	Improvements in graphene growth on 4H-SiC(0001) using plasma induced surface oxidation. <i>Journal of Applied Physics</i> , 2019, 126, 065301.	1.1	2
25	Highly efficient planarization of sliced 4H-SiC (0001) wafer by slurryless electrochemical mechanical polishing. <i>International Journal of Machine Tools and Manufacture</i> , 2019, 144, 103431.	6.2	48
26	Etching Characteristics of Quartz Crystal Wafers Using Argon-Based Atmospheric Pressure CF <sub>4</sub> Plasma Stabilized by Ethanol Addition. <i>Nanomanufacturing and Metrology</i> , 2019, 2, 168-176.	1.5	13
27	Influence of air contamination during heat-assisted plasma treatment on adhesion properties of polytetrafluoroethylene (PTFE). <i>RSC Advances</i> , 2019, 9, 22900-22906.	1.7	8
28	Obtaining Atomically Smooth 4H-SiC (0001) Surface by Controlling Balance Between Anodizing and Polishing in Electrochemical Mechanical Polishing. <i>Nanomanufacturing and Metrology</i> , 2019, 2, 140-147.	1.5	27
29	Improved Catalytic Durability of Pt-Particle/ABS for H <sub>2</sub> O <sub>2</sub> Decomposition in Contact Lens Cleaning. <i>Nanomaterials</i> , 2019, 9, 342.	1.9	2
30	Ultrasonic-assisted anodic oxidation of 4H-SiC (0001) surface. <i>Electrochemistry Communications</i> , 2019, 100, 1-5.	2.3	26
31	Surface Modification and Microstructuring of 4H-SiC(0001) by Anodic Oxidation with Sodium Chloride Aqueous Solution. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 2535-2542.	4.0	16
32	Effect of rubber compounding agent on adhesion strength between rubber and heat-assisted plasma-treated polytetrafluoroethylene (PTFE). <i>Journal of Adhesion</i> , 2019, 95, 242-257.	1.8	14
33	Investigation of anodic oxidation mechanism of 4H-SiC (0001) for electrochemical mechanical polishing. <i>Electrochimica Acta</i> , 2018, 271, 666-676.	2.6	39
34	Optimization of Gas Composition Used in Plasma Chemical Vaporization Machining for Figuring of Reaction-Sintered Silicon Carbide with Low Surface Roughness. <i>Scientific Reports</i> , 2018, 8, 2376.	1.6	11
35	Damage-free highly efficient polishing of single-crystal diamond wafer by plasma-assisted polishing. <i>CIRP Annals - Manufacturing Technology</i> , 2018, 67, 353-356.	1.7	43
36	Atomic-scale finishing of carbon face of single crystal SiC by combination of thermal oxidation pretreatment and slurry polishing. <i>Applied Surface Science</i> , 2018, 434, 40-48.	3.1	29

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37	Development of Damage-free Figuring and Finishing Techniques for Ceramics Materials by Utilizing Reactive Plasma. Funtai Oyobi Fummatsumu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2018, 65, 654-658.	0.1	0
38	AFM Observation of Initial Oxidation Stage of 4H-SiC (0001) in Electrochemical Mechanical Polishing. Procedia CIRP, 2018, 68, 735-740.	1.0	11
39	Adhesive-free adhesion between heat-assisted plasma-treated fluoropolymers (PTFE, PFA) and plasma-jet-treated polydimethylsiloxane (PDMS) and its application. Scientific Reports, 2018, 8, 18058.	1.6	45
40	Surface Modification of Fluoropolymer Using Open-Air Plasma Treatment at Atmospheric Pressure with Ar, Ar <sub>1/4</sub> O <sub>2</sub> , and Ar <sub>1/4</sub> H <sub>2</sub> for Application in High Adhesion Metal Wiring Patterns. Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan, 2018, 69, 155-162.	0.1	2
41	Improving the grindability of titanium alloy Ti-6Al-4V with the assistance of ultrasonic vibration and plasma electrolytic oxidation. CIRP Annals - Manufacturing Technology, 2017, 66, 345-348.	1.7	24
42	Polishing of Tungsten Carbide by Combination of Anodizing and Silica Slurry Polishing. Journal of the Electrochemical Society, 2017, 164, E352-E359.	1.3	11
43	Drastic Improvement in Adhesion Property of Polytetrafluoroethylene (PTFE) via Heat-Assisted Plasma Treatment Using a Heater. Scientific Reports, 2017, 7, 9476.	1.6	35
44	Damage-free finishing of CVD-SiC by a combination of dry plasma etching and plasma-assisted polishing. International Journal of Machine Tools and Manufacture, 2017, 115, 38-46.	6.2	45
45	Radiolytic Synthesis of Pt-Particle/ABS Catalysts for H <sub>2</sub> O <sub>2</sub> Decomposition in Contact Lens Cleaning. Nanomaterials, 2017, 7, 235.	1.9	7
46	Investigation on the formation of projections and cracks in anodic oxidation of reaction-sintered silicon carbide. IOP Conference Series: Materials Science and Engineering, 2017, 167, 012064.	0.3	1
47	Preliminary study on atmospheric-pressure plasma-based chemical dry figuring and finishing of reaction-sintered silicon carbide. Optical Engineering, 2016, 55, 105102.	0.5	7
48	Improvement in Adhesion between Polytetrafluoroethylene (PTFE) and Electroless-Plated Copper Film Using Heat-Assisted Plasma Treatment. Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan, 2016, 67, 551-556.	0.1	10
49	Comparative analysis on surface property in anodic oxidation polishing of reaction-sintered silicon carbide and single-crystal 4H silicon carbide. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	14
50	Neutron Focusing by a Kirkpatrick-Baez Type Super-Mirror. , 2015, , .		0
51	Atomic-scale and pit-free flattening of GaN by combination of plasma pretreatment and time-controlled chemical mechanical polishing. Applied Physics Letters, 2015, 107, .	1.5	13
52	Electro-chemical mechanical polishing of single-crystal SiC using CeO <sub>2</sub> slurry. Electrochemistry Communications, 2015, 52, 5-8.	2.3	86
53	Mechanism analysis on finishing of reaction-sintered silicon carbide by combination of water vapor plasma oxidation and ceria slurry polishing. Optical Engineering, 2015, 54, 055106.	0.5	14
54	Competition between surface modification and abrasive polishing: a method of controlling the surface atomic structure of 4H-SiC (0001). Scientific Reports, 2015, 5, 8947.	1.6	40

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55	Plasma-assisted polishing of gallium nitride to obtain a pit-free and atomically flat surface. CIRP Annals - Manufacturing Technology, 2015, 64, 531-534.	1.7	47
56	Efficient processing of reaction-sintered silicon carbide by anodically oxidation-assisted polishing. Optical Engineering, 2015, 54, 105113.	0.5	7
57	Comparison of thermal oxidation and plasma oxidation of 4H-SiC (0001) for surface flattening. Applied Physics Letters, 2014, 104, .	1.5	17
58	Observation of the Spatial Distribution of Gravitationally Bound Quantum States of Ultracold Neutrons and Its Derivation Using the Wigner Function. Physical Review Letters, 2014, 112, 071101.	2.9	30
59	Investigation of Removal Mechanism of Sapphire in Plasma Assisted Polishing. Key Engineering Materials, 2014, 625, 458-462.	0.4	6
60	Optimization of the plasma oxidation and abrasive polishing processes in plasma-assisted polishing for highly effective planarization of 4H-SiC. CIRP Annals - Manufacturing Technology, 2014, 63, 529-532.	1.7	42
61	Characterization of 4H-SiC (0001) surface processed by plasma-assisted polishing. International Journal of Advanced Manufacturing Technology, 2014, 72, 1-7.	1.5	33
62	Atomic-scale flattening mechanism of 4H-SiC (0 0 0 1) in plasma assisted polishing. CIRP Annals - Manufacturing Technology, 2013, 62, 575-578.	1.7	57
63	Ultrasoother reaction-sintered silicon carbide surface resulting from combination of thermal oxidation and ceria slurry polishing. Optics Express, 2013, 21, 14780.	1.7	19
64	Atomic-scale planarization of 4H-SiC (0001) by combination of thermal oxidation and abrasive polishing. Applied Physics Letters, 2013, 103, 111603.	1.5	17
65	Figuring of Neutron Focusing Elliptical Mirror Substrate by Numerically Controlled Local Wet Etching. Journal of the Japan Society for Precision Engineering, 2013, 79, 813-817.	0.0	0
66	Quadruple Stacked Elliptical Supermirror Device for One Dimensional Neutron Focusing. Key Engineering Materials, 2012, 523-524, 272-275.	0.4	1
67	Figuring of Aspherical Metal Mirror Substrate for Neutron Focusing by Numerically Controlled Electrochemical Machining. Key Engineering Materials, 2012, 523-524, 29-33.	0.4	2
68	Effect of Si interlayers on the magnetic and mechanical properties of Fe/Ge neutron polarizing multilayer mirrors. Journal of Applied Physics, 2012, 111, 063904.	1.1	7
69	The Improvement of Removal Function in Local Wet Etching by Using Eccentric Rotation System. Key Engineering Materials, 2012, 516, 504-509.	0.4	4
70	A Simulation Study on Figure Error Correction Using Near-Gaussian Removal Function in Numerical Controlled Local Wet Etching. Key Engineering Materials, 2012, 523-524, 276-280.	0.4	3
71	Noncontact Figuring of Millimeter-Thick Elliptical Mirror Substrate by Numerically Controlled Local Wet Etching. Key Engineering Materials, 2012, 516, 361-366.	0.4	1
72	One-dimensional neutron focusing with large beam divergence by 400mm-long elliptical supermirror. Journal of Physics: Conference Series, 2012, 340, 012034.	0.3	8

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73	High-precision figured thin supermirror substrates for multiple neutron focusing device. Journal of Physics: Conference Series, 2012, 340, 012016.	0.3	6
74	Preliminary Study on Chemical Figuring and Finishing of Sintered SiC Substrate Using Atmospheric Pressure Plasma. Procedia CIRP, 2012, 3, 335-339.	1.0	15
75	Improvement in Thickness Uniformity of Thick SOI by Numerically Controlled Local Wet Etching. Journal of Nanoscience and Nanotechnology, 2011, 11, 2910-2915.	0.9	0
76	Finishing of AT-Cut Quartz Crystal Wafer with Nanometric Thickness Uniformity by Pulse-Modulated Atmospheric Pressure Plasma Etching. Journal of Nanoscience and Nanotechnology, 2011, 11, 2922-2927.	0.9	0
77	Plasma assisted polishing of single crystal SiC for obtaining atomically flat strain-free surface. CIRP Annals - Manufacturing Technology, 2011, 60, 571-574.	1.7	135
78	Development of fabrication process for aspherical neutron focusing mirror using numerically controlled local wet etching with low-pressure polishing. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2011, 634, S112-S116.	0.7	15
79	Evaluation of Surface Roughness of Quartz Glass Substrate in Fabrication Process for Neutron Focusing Mirror. Advanced Materials Research, 2011, 325, 647-652.	0.3	0
80	Damage-Free Dry Polishing of 4H-SiC Combined with Atmospheric-Pressure Water Vapor Plasma Oxidation. Japanese Journal of Applied Physics, 2011, 50, 08JG05.	0.8	9
81	High-reflectivity (m=4) elliptical neutron focusing supermirror fabricated by numerically controlled local wet etching with ion beam sputter deposition. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2010, 616, 193-196.	0.7	10
82	Fabrication of damage-free Johansson-type doubly curved crystal spectrometer substrate by numerically controlled local wet etching. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2010, 616, 281-284.	0.7	4
83	Breaking the 10 $\mu$ m barrier in hard-X-ray focusing. Nature Physics, 2010, 6, 122-125.	6.5	484
84	Atmospheric pressure plasma liquid deposition of copper nanoparticles onto poly(4-vinylpyridine)-grafted-poly(tetrafluoroethylene) surface. Transactions of the Materials Research Society of Japan, 2010, 35, 817-820.	0.2	4
85	High-Integrity Finishing of 4H-SiC (0001) by Plasma-Assisted Polishing. Advanced Materials Research, 2010, 126-128, 423-428.	0.3	27
86	Fabrication of plano-elliptical neutron focusing supermirror by numerically controlled local wet etching with ion beam sputter deposition. Journal of Physics: Conference Series, 2010, 251, 012077.	0.3	2
87	Neutron beam focusing using large-m supermirrors coated on precisely-figured aspheric surfaces. Journal of Physics: Conference Series, 2010, 251, 012076.	0.3	2
88	Improvement of thickness uniformity of bulk silicon wafer by numerically controlled local wet etching. Journal of Crystal Growth, 2009, 311, 2560-2563.	0.7	2
89	Figuring of plano-elliptical neutron focusing mirror by local wet etching. Optics Express, 2009, 17, 6414.	1.7	30
90	Figuring of elliptical hard X-ray focusing mirror using 1 $\mu$ m dimensional numerically controlled local wet etching. Surface and Interface Analysis, 2008, 40, 1014-1018.	0.8	2

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91	Uniformalization of AT cut quartz crystal wafer thickness using open-air type plasma CVM process. Surface and Interface Analysis, 2008, 40, 1007-1010.	0.8	1
92	Etching characteristics of local wet etching of silicon in HF/HNO <sub>3</sub> mixtures. Surface and Interface Analysis, 2008, 40, 1011-1013.	0.8	21
93	Etching characteristics of GaN by plasma chemical vaporization machining. Surface and Interface Analysis, 2008, 40, 1566-1570.	0.8	8
94	Damage-free improvement of thickness uniformity of quartz crystal wafer by plasma chemical vaporization machining. CIRP Annals - Manufacturing Technology, 2008, 57, 567-570.	1.7	48
95	Surface Gradient Integrated Profiler for X-ray and EUV Optics—Calibration of the rotational angle error of the rotary encoders. AIP Conference Proceedings, 2007, , .	0.3	0
96	Fabrication of X-ray Mirror for Hard X-ray Diffraction Limited Nanofocusing. AIP Conference Proceedings, 2007, , .	0.3	0
97	Ultraprecision Machining Method for Ultraprecise Aspherical Mirror. The Review of Laser Engineering, 2007, 35, 162-167.	0.0	0
98	Efficient focusing of hard x rays to 25nm by a total reflection mirror. Applied Physics Letters, 2007, 90, 051903.	1.5	203
99	Development of numerically controlled local wet etching. Science and Technology of Advanced Materials, 2007, 8, 158-161.	2.8	24
100	Fabrication of Ultra Precision Optics by Numerically Controlled Local Wet Etching. CIRP Annals - Manufacturing Technology, 2007, 56, 541-544.	1.7	40
101	Surface gradient integrated profiler for X-ray and EUV optics. Science and Technology of Advanced Materials, 2007, 8, 177-180.	2.8	5
102	Improvement of the Thickness Distribution of AT Cut Quartz Crystal Wafer by Open-air Type Plasma Chemical Vaporization Machining. E-Journal of Surface Science and Nanotechnology, 2007, 5, 41-44.	0.1	3
103	Ultraprecision Finishing Process for Improving Thickness Distribution of Quartz Crystal Wafer by Utilizing Atmospheric Pressure Plasma. , 2006, , .		0
104	Polishing Characteristics of Silicon Carbide by Plasma Chemical Vaporization Machining. Japanese Journal of Applied Physics, 2006, 45, 8277-8280.	0.8	26
105	Ultraprecision Machining Utilizing Numerically Controlled Scanning of Localized Atmospheric Pressure Plasma. Japanese Journal of Applied Physics, 2006, 45, 8270-8276.	0.8	20
106	Development of mirror manipulator for hard-x-ray nanofocusing at sub-50-nm level. Review of Scientific Instruments, 2006, 77, 093107.	0.6	32
107	Development of scanning x-ray fluorescence microscope with spatial resolution of 30nm using Kirkpatrick-Baez mirror optics. Review of Scientific Instruments, 2006, 77, 103102.	0.6	85
108	Creation of perfect surfaces. Journal of Crystal Growth, 2005, 275, 39-50.	0.7	52

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109	Relative angle determinable stitching interferometry for hard x-ray reflective optics. Review of Scientific Instruments, 2005, 76, 045102.	0.6	119
110	Improvement of the thickness distribution of a quartz crystal wafer by numerically controlled plasma chemical vaporization machining. Review of Scientific Instruments, 2005, 76, 096103.	0.6	16
111	Diffraction-limited two-dimensional hard-x-ray focusing at the 100nm level using a Kirkpatrick-Baez mirror arrangement. Review of Scientific Instruments, 2005, 76, 083114.	0.6	33
112	Fabrication of elliptically figured mirror for focusing hard x rays to size less than 50nm. Review of Scientific Instruments, 2005, 76, 063708.	0.6	63
113	Thinning of silicon-on-insulator wafers by numerically controlled plasma chemical vaporization machining. Review of Scientific Instruments, 2004, 75, 942-946.	0.6	40
114	Fabrication technology of hard x-ray aspherical mirror optics and application to nanospectroscopy. , 2004, , .		9
115	Development of a figure correction method having spatial resolution close to 0.1 mm. , 2004, 5193, 105.		4
116	Fabrication of elliptical mirror at nanometer-level accuracy for hard x-ray focusing by numerically controlled plasma chemical vaporization machining. Review of Scientific Instruments, 2003, 74, 4549-4553.	0.6	99
117	Two-dimensional Submicron Focusing of Hard X-rays by Two Elliptical Mirrors Fabricated by Plasma Chemical Vaporization Machining and Elastic Emission Machining. Japanese Journal of Applied Physics, 2003, 42, 7129-7134.	0.8	57
118	Microstitching interferometry for x-ray reflective optics. Review of Scientific Instruments, 2003, 74, 2894-2898.	0.6	149
119	Aspheric Surface Fabrication in nm-level Accuracy by Numerically Controlled Plasma Chemical Vaporization Machining (CVM) and Elastic Emission Machining (EEM). , 2002, 4782, 265.		9
120	Submicron focusing of hard x-ray beam by elliptically figured mirrors for scanning x-ray microscopy. , 2002, , .		10
121	Wave-optical analysis of submicron focus of hard x-ray beams by reflective optics. , 2002, 4782, 271.		17
122	Fabrication of optics by use of plasma chemical vaporization machining with a pipe electrode. Applied Optics, 2002, 41, 3971.	2.1	32
123	Deterministic retrieval of surface waviness by means of topography with coherent X-rays. Journal of Synchrotron Radiation, 2002, 9, 223-228.	1.0	26
124	Nearly diffraction-limited line focusing of a hard-X-ray beam with an elliptically figured mirror. Journal of Synchrotron Radiation, 2002, 9, 313-316.	1.0	62
125	Development of plasma chemical vaporization machining and elastic emission machining systems for coherent x-ray optics. , 2001, 4501, 30.		39
126	Development of plasma chemical vaporization machining. Review of Scientific Instruments, 2000, 71, 4627.	0.6	108



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127	The study of fabrication of the x-ray mirror by numerically controlled plasma chemical vaporization machining: Development of the machine for the x-ray mirror fabrication. Review of Scientific Instruments, 2000, 71, 4620.	0.6	60
128	First-principles simulations of removal process in EEM (Elastic Emission Machining). Computational Materials Science, 1999, 14, 232-235.	1.4	48
129	Computer numerically controlled plasma chemical vaporization machining with a pipe electrode for optical fabrication. Applied Optics, 1998, 37, 5198.	2.1	50
130	Plasma Chemical Vaporization Machining (CVM) for Fabrication of Optics. Japanese Journal of Applied Physics, 1998, 37, L894-L896.	0.8	10
131	Laser beam intensity profile transformation with a fabricated mirror. Applied Optics, 1997, 36, 551.	2.1	24
132	Plasma CVM (chemical vaporization machining): an ultra precision machining technique using high-pressure reactive plasma. Nanotechnology, 1993, 4, 225-229.	1.3	56
133	Plasma-CVM (Chemical Vaporization Machining). , 0, , 587-606.		1
134	Temperature Dependence of Plasma Chemical Vaporization Machining of Silicon and Silicon Carbide. Materials Science Forum, 0, 600-603, 847-850.	0.3	17
135	Figuring of Elliptical Neutron Focusing Mirror Using Numerically Controlled Local Wet Etching. Key Engineering Materials, 0, 407-408, 376-379.	0.4	0
136	Improvement of Thickness Uniformity of Bulk Silicon Wafer by Numerically Controlled Local Wet Etching. Key Engineering Materials, 0, 407-408, 372-375.	0.4	0
137	Fabrication of Ultraprecision Millimeter-Thick Elliptical Neutron Focusing Mirror Substrate by Local Wet Etching. Key Engineering Materials, 0, 447-448, 208-212.	0.4	0
138	Study on &lt;i>In Situ &lt;/i>Etching Rate Monitoring in Numerically Controlled Local Wet Etching. Key Engineering Materials, 0, 523-524, 34-39.	0.4	0
139	Evaluation of Surface Roughness and Subsurface Damage of 4H-SiC Processed by Different Finishing Techniques. Key Engineering Materials, 0, 523-524, 19-23.	0.4	2
140	Preliminary Study on Highly Efficient Polishing of 4H-SiC by Utilization of Anodic Oxidation. Advanced Materials Research, 0, 1017, 509-514.	0.3	13
141	Study on Removal Mechanism of Sapphire in Plasma Assisted Polishing. Advanced Materials Research, 0, 1136, 317-320.	0.3	4